



# RF Power Field Effect Transistor

## N-Channel Enhancement-Mode Lateral MOSFETs

Designed primarily for pulsed wideband large-signal output and driver applications with frequencies up to 450 MHz. Devices are unmatched and are suitable for use in industrial, medical and scientific applications.

- Typical CW Performance at 220 MHz:  $V_{DD} = 50$  Volts,  $I_{DQ} = 900$  mA,  $P_{out} = 300$  Watts  
 Power Gain — 27 dB  
 Drain Efficiency — 68%
- Capable of Handling 10:1 VSWR, @ 50 Vdc, 210 MHz, 300 Watts CW Output Power

### Features

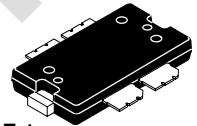
- Integrated ESD Protection
- Greater Negative Gate-Source Voltage Range for Improved Class C Operation
- Excellent Thermal Stability
- Facilitates Manual Gain Control, ALC and Modulation Techniques
- 225°C Capable Plastic Package
- RoHS Compliant

**MRF6V2300N**  
**MRF6V2300NB**

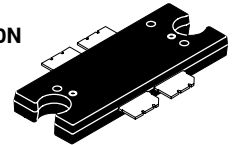
PREPRODUCTION

**10-450 MHz, 300 W, 50 V**  
**LATERAL N-CHANNEL**  
**SINGLE-ENDED**  
**BROADBAND**  
**RF POWER MOSFETs**

**CASE 1486-03, STYLE 1**  
**TO-270 WB-4**  
**PLASTIC**  
**MRF6V2300N**



**CASE 1484-04, STYLE 1**  
**TO-272 WB-4**  
**PLASTIC**  
**MRF6V2300NB**



**PARTS ARE SINGLE-ENDED**

**Table 1. Maximum Ratings**

Rating	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	-0.5, +110	Vdc
Gate-Source Voltage	$V_{GS}$	-6.0, +10	Vdc
Storage Temperature Range	$T_{stg}$	-65 to +150	°C
Operating Junction Temperature (1,2)	$T_J$	225	°C

**Table 2. Thermal Characteristics**

Characteristic	Symbol	Value (3)	Unit
Thermal Resistance, Junction to Case Case Temperature TBD°C, TBD W CW Case Temperature TBD°C, TBD W CW	$R_{\theta JC}$	TBD TBD	°C/W

1. Continuous use at maximum temperature will affect MTTF.
2. MTTF calculator available at <http://www.freescale.com/rf>. Select Tools/Software/Application Software/Calculators to access the MTTF calculators by product. (Calculator available when part is in production.)
3. Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <http://www.freescale.com/rf>. Select Documentation/Application Notes - AN1955.

This document contains information on a preproduction product. Specifications and information herein are subject to change without notice.

**Table 3. ESD Protection Characteristics**

Test Methodology	Class
Human Body Model (per JESD22-A114)	TBD (Minimum)
Machine Model (per EIA/JESD22-A115)	TBD (Minimum)
Charge Device Model (per JESD22-C101)	TBD (Minimum)

**Table 4. Moisture Sensitivity Level**

Test Methodology	Rating	Package Peak Temperature	Unit
Per JESD 22-A113, IPC/JEDEC J-STD-020	3	260	°C

**Table 5. Electrical Characteristics** ( $T_C = 25^\circ\text{C}$  unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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**Off Characteristics**

Zero Gate Voltage Drain Leakage Current ( $V_{DS} = 110\text{ Vdc}$ , $V_{GS} = 0\text{ Vdc}$ )	$I_{DSS}$	—	—	10	$\mu\text{A}$
Zero Gate Voltage Drain Leakage Current ( $V_{DS} = 50\text{ Vdc}$ , $V_{GS} = 0\text{ Vdc}$ )	$I_{DSS}$	—	—	10	$\mu\text{A}$
Drain-Source Breakdown Voltage ( $I_D = 150\text{ mA}$ , $V_{GS} = 0\text{ Vdc}$ )	$BV_{DSS}$	110	—	—	Vdc
Gate-Source Leakage Current ( $V_{GS} = 5\text{ Vdc}$ , $V_{DS} = 0\text{ Vdc}$ )	$I_{GSS}$	—	—	10	$\mu\text{A}$

**On Characteristics**

Gate Threshold Voltage ( $V_{DS} = 10\text{ Vdc}$ , $I_D = 800\ \mu\text{A}$ )	$V_{GS(th)}$	—	2.4	—	Vdc
Drain-Source On-Voltage ( $V_{GS} = 10\text{ Vdc}$ , $I_D = 2\text{ A}$ )	$V_{DS(on)}$	—	0.3	—	Vdc

**Dynamic Characteristics**

Reverse Transfer Capacitance ( $V_{DS} = 50\text{ Vdc} \pm 30\text{ mV(rms)}$ ac @ 1 MHz, $V_{GS} = 0\text{ Vdc}$ )	$C_{rss}$	—	2.44	—	pF
Output Capacitance ( $V_{DS} = 50\text{ Vdc} \pm 30\text{ mV(rms)}$ ac @ 1 MHz, $V_{GS} = 0\text{ Vdc}$ )	$C_{oss}$	—	120	—	pF
Input Capacitance ( $V_{DS} = 50\text{ Vdc} \pm 30\text{ mV(rms)}$ ac @ 1 MHz, $V_{GS} = 0\text{ Vdc}$ )	$C_{iss}$	—	282	—	pF

**Functional Tests** (In Freescale Test Fixture, 50 ohm system)  $V_{DD} = 50\text{ Vdc}$ ,  $I_{DQ} = 900\text{ mA}$ ,  $P_{out} = 300\text{ W}$ ,  $f = 220\text{ MHz}$ , CW

Power Gain	$G_{ps}$	—	27	—	dB
Drain Efficiency	$\eta_D$	—	68	—	%
Input Return Loss	IRL	—	-17	—	dB
$P_{out}$ @ 1 dB Compression Point, CW ( $f = 220\text{ MHz}$ )	P1dB	—	330	—	W



ATTENTION: The MRF6V2300N and MRF6V2300NB are high power devices and special considerations must be followed in board design and mounting. Incorrect mounting can lead to internal temperatures which exceed the maximum allowable operating junction temperature. Refer to Freescale Application Note AN3263 (for bolt down mounting) or AN1907 (for solder reflow mounting) **PRIOR TO STARTING SYSTEM DESIGN** to ensure proper mounting of these devices.

## TYPICAL CHARACTERISTICS

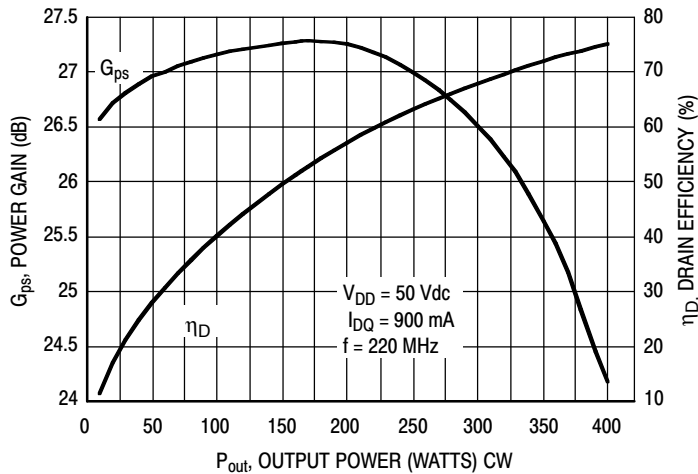


Figure 1. Power Gain and Drain Efficiency versus CW Output Power

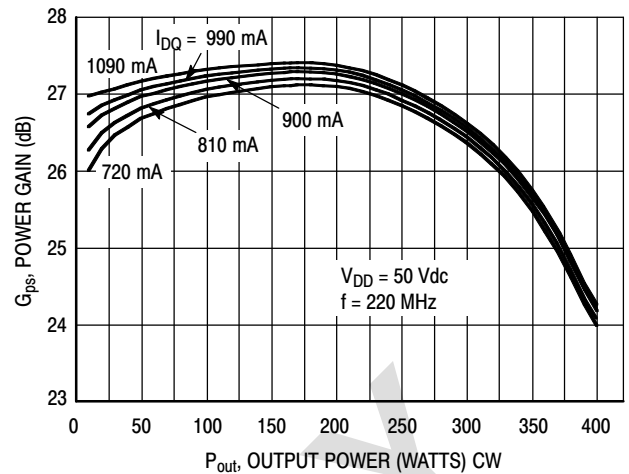


Figure 2. Power Gain versus Output Power

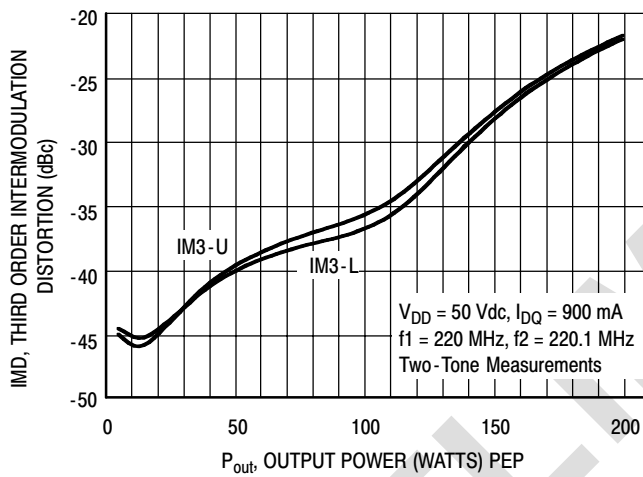


Figure 3. Third Order Intermodulation Distortion versus Output Power

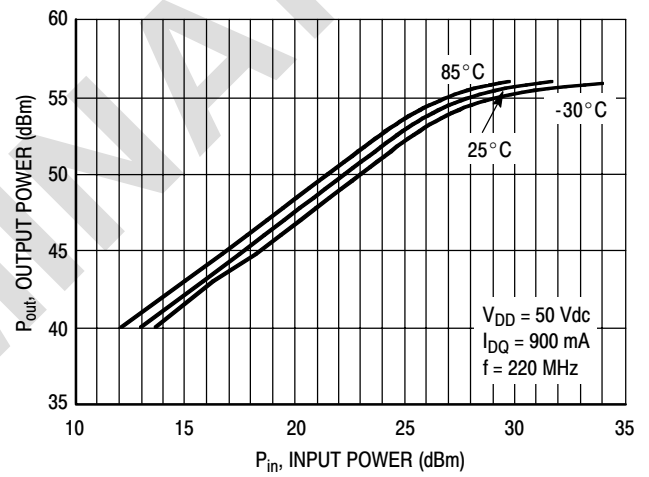
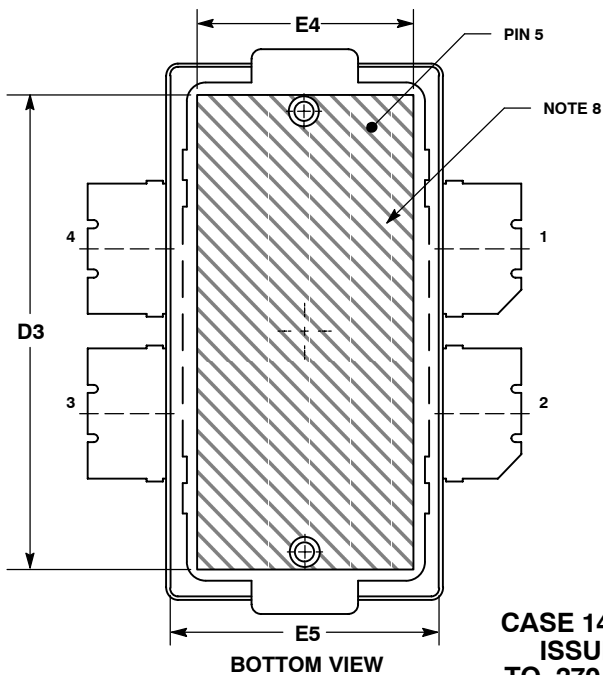
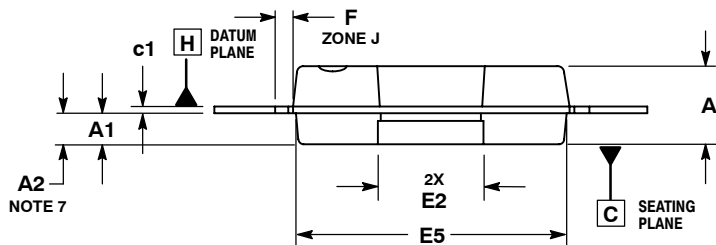
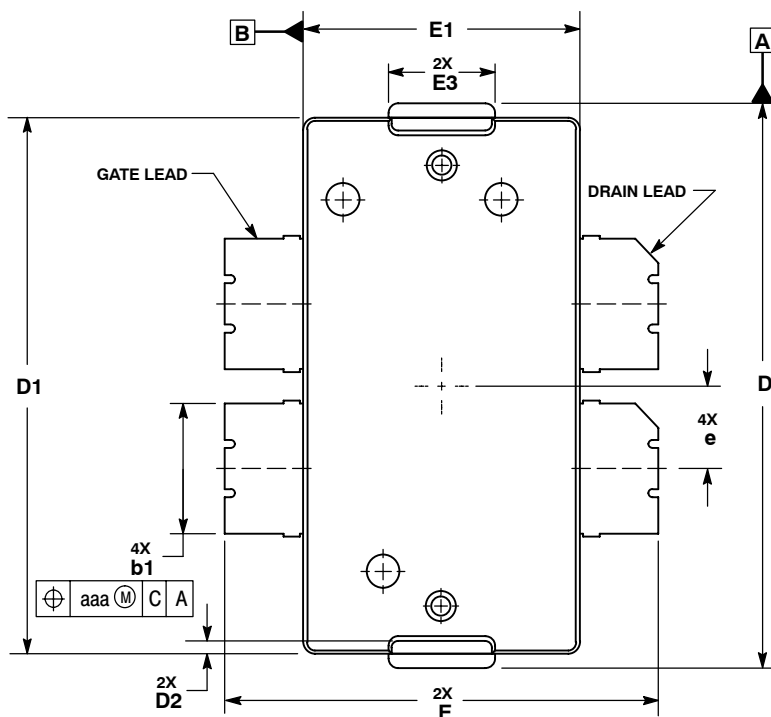


Figure 4. Output Power versus Input Power over Temperature

# PACKAGE DIMENSIONS



**CASE 1486-03  
ISSUE C  
TO-270 WB-4  
PLASTIC  
MRF6V2300N**

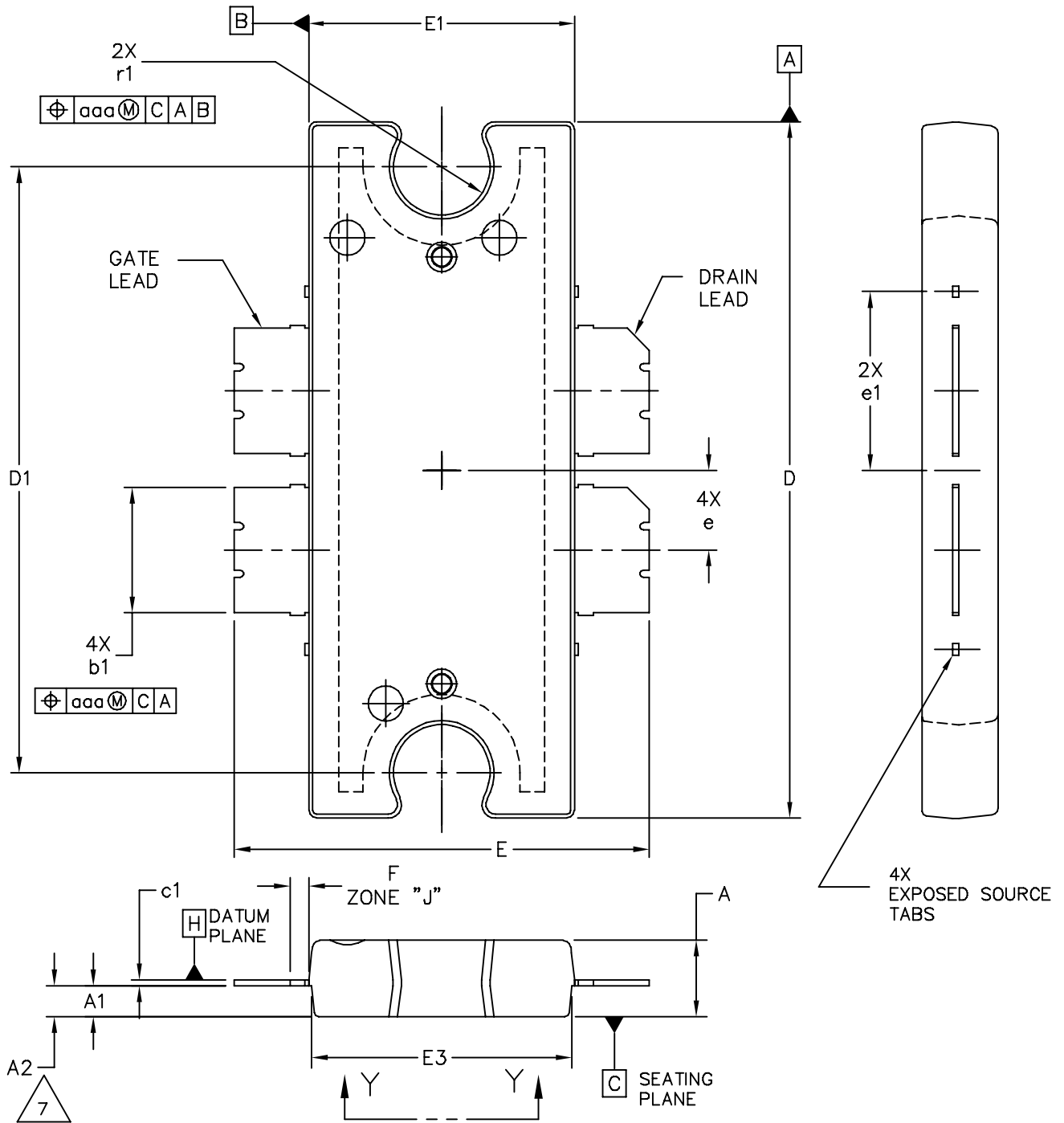
**NOTES:**

1. CONTROLLING DIMENSION: INCH.
2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M-1994.
3. DATUM PLANE -H- IS LOCATED AT THE TOP OF LEAD AND IS COINCIDENT WITH THE LEAD WHERE THE LEAD EXITS THE PLASTIC BODY AT THE TOP OF THE PARTING LINE.
4. DIMENSIONS "D" AND "E1" DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS .006 PER SIDE. DIMENSIONS "D" AND "E1" DO INCLUDE MOLD MISMATCH AND ARE DETERMINED AT DATUM PLANE -H-.
5. DIMENSION "b1" DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE .005 TOTAL IN EXCESS OF THE "b1" DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. DATUMS -A- AND -B- TO BE DETERMINED AT DATUM PLANE -H-.
7. DIMENSION A2 APPLIES WITHIN ZONE "J" ONLY.
8. HATCHING REPRESENTS THE EXPOSED AREA OF THE HEAT SLUG.

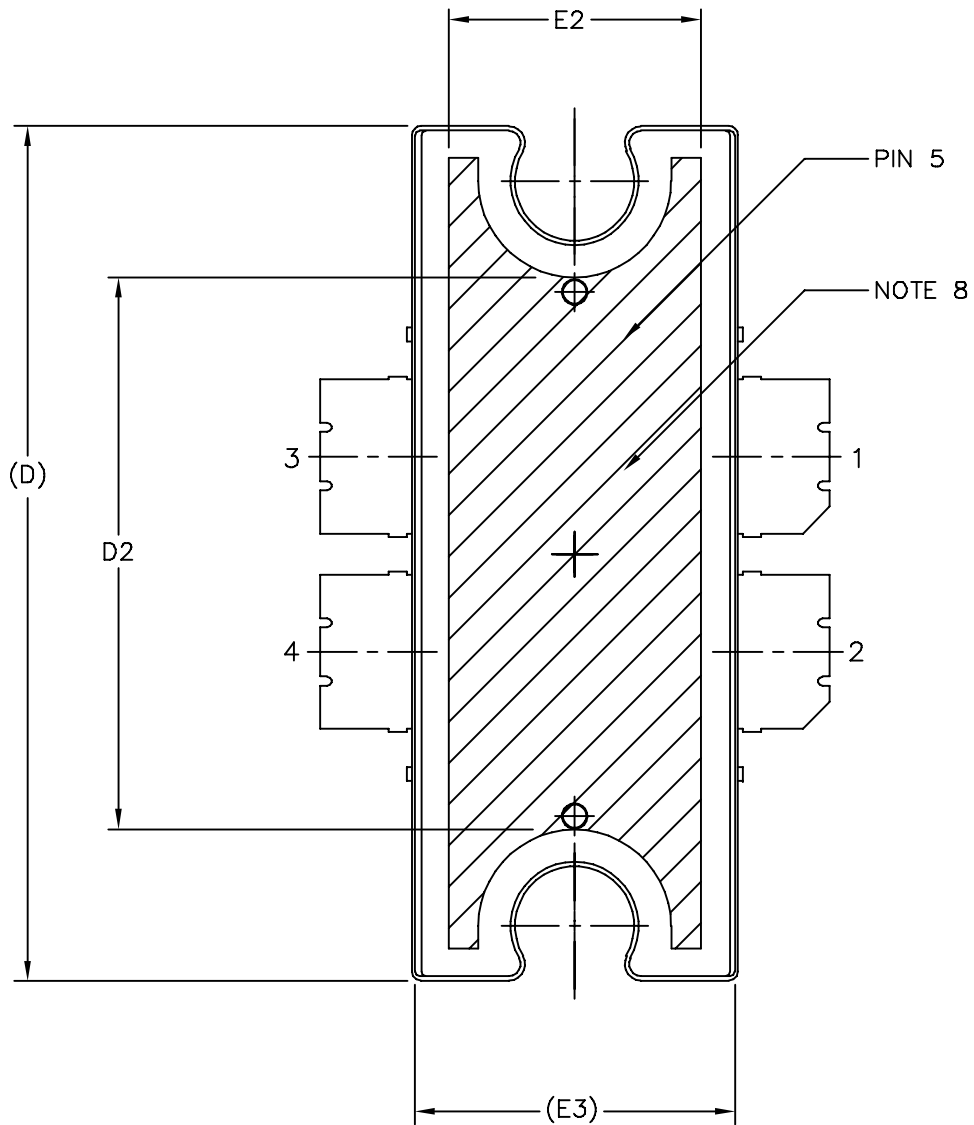
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.100	.104	2.54	2.64
A1	.039	.043	0.99	1.09
A2	.040	.042	1.02	1.07
D	.712	.720	18.08	18.29
D1	.688	.692	17.48	17.58
D2	.011	.019	0.28	0.48
D3	.600	---	15.24	---
E	.551	.559	14	14.2
E1	.353	.357	8.97	9.07
E2	.132	.140	3.35	3.56
E3	.124	.132	3.15	3.35
E4	.270	---	6.86	---
E5	.346	.350	8.79	8.89
F	.025 BSC		0.64 BSC	
b1	.164	.170	4.17	4.32
c1	.007	.011	0.18	0.28
e	.106 BSC		2.69 BSC	
aaa	.004		0.10	

**STYLE 1:**

1. DRAIN
2. DRAIN
3. GATE
4. GATE
5. SOURCE



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TITLE: <p style="text-align: center;">TO-272 4 LEAD, WIDE BODY</p>	DOCUMENT NO: 98ASA10575D	REV: D
	CASE NUMBER: 1484-04	05 APR 2006
	STANDARD: NON-JEDEC	



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NOTES:

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3. DATUM PLANE H IS LOCATED AT THE TOP OF LEAD AND IS COINCIDENT WITH THE LEAD WHERE THE LEAD EXITS THE PLASTIC BODY AT THE TOP OF THE PARTING LINE.
4. DIMENSIONS "D" AND "E1" DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS .006 PER SIDE. DIMENSIONS "D" AND "E1" DO INCLUDE MOLD MISMATCH AND ARE DETERMINED AT DATUM PLANE H.
5. DIMENSIONS "b1" DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE .005 TOTAL IN EXCESS OF THE "b1" DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. DATUM A AND B TO BE DETERMINED AT DATUM PLANE H.
7. DIMENSION A2 APPLIES WITHIN ZONE "J" ONLY.
8. HATCHING REPRESENTS EXPOSED AREA OF THE HEAT SLUG. HATCHED AREA SHOWN IS ON THE SAME PLANE.

STYLE 1:

PIN 1 - DRAIN      PIN 2 - DRAIN  
 PIN 3 - GATE      PIN 4 - GATE  
 PIN 5 - SOURCE

DIM	INCH		MILLIMETER		DIM	INCH		MILLIMETER	
	MIN	MAX	MIN	MAX		MIN	MAX	MIN	MAX
A	.100	.104	2.54	2.64	b1	.164	.170	4.17	4.32
A1	.039	.043	0.99	1.09	c1	.007	.011	.18	.28
A2	.040	.042	1.02	1.07	r1	.063	.068	1.60	1.73
D	.928	.932	23.57	23.67	e	.106 BSC		2.69 BSC	
D1	.810 BSC		20.57 BSC		e1	.239 INFO ONLY		6.07 INFO ONLY	
D2	.600	---	15.24	---	aaa	.004		.10	
E	.551	.559	14	14.2					
E1	.353	.357	8.97	9.07					
E2	.270	---	6.86	---					
E3	.346	.350	8.79	8.89					
F	.025 BSC		0.64 BSC						

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**MECHANICAL OUTLINE**

PRINT VERSION NOT TO SCALE

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TO-272  
 4 LEAD WIDE BODY

DOCUMENT NO: 98ASA10575D

REV: D

CASE NUMBER: 1484-04

05 APR 2006

STANDARD: NON-JEDEC

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